IN THE SPECIFICATION

Pages 22 and 23, the paragraph bridging these pages from page 22, line 17 to page 23, line 4, replace the bridging paragraph with:

The carrier having the high frequency circuit as described above is mounted on the Peltier cooler 4. The Peltier cooler is denoted by reference 4 in Fig. 5. The Peltier cooler 4 is fixed at the bottom of the containment case 5. When a predetermined current is supplied by way of leads (9, 10,) 10 of the Peltier cooler 4, heat absorption occurs on the upper side of the Peltier cooler 4 to cool the sub-mount 2 and the semiconductor laser chip 1 on the carrier 3. Further, by reversing the polarity of the current supplied, heat can be added to the chip to elevate the chip temperature. Reference ½ 9 in Fig. 5 denotes a thermister that monitors the temperature by the resistance and keeps the driving temperature of the laser constant at a set temperature.

Page 24, the second full paragraph, lines 15 to 17, replace the paragraph with:

This embodiment is an example in which a laser region having a plurality of active regions, a modulation chip region and a multiplexer are integrated in are on one substrate.